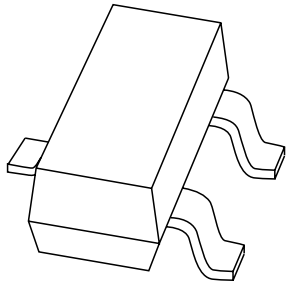


DATA SHEET



BF821; BF823 PNP high-voltage transistors

Product data sheet
Supersedes data of 1999 Apr 15

2004 Jan 16



PNP high-voltage transistors

BF821; BF823

FEATURES

- Low current (max. 50 mA)
- High voltage (max. 300 V).

APPLICATIONS

- Telephony and professional communication equipment.

DESCRIPTION

PNP transistor in a SOT23 plastic package.
NPN complements: BF820, BF822.

MARKING

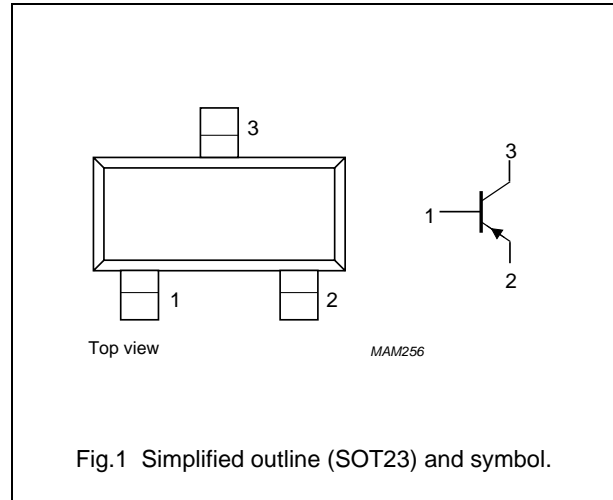
TYPE NUMBER	MARKING CODE ⁽¹⁾
BF821	1W*
BF823	1Y*

Note

- * = p : Made in Hong Kong.
* = t : Made in Malaysia.
* = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPENUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BF821	–	plastic surface mounted package; 3 leads	SOT23
BF823	–	plastic surface mounted package; 3 leads	SOT23

PNP high-voltage transistors

BF821; BF823

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter	–	–300	V
	BF821				
V _{CEO}	collector-emitter voltage	open base	–	–300	V
	BF823				
V _{EBO}	emitter-base voltage	open collector	–	–5	V
I _C	collector current (DC)		–	–50	mA
I _{CM}	peak collector current		–	–100	mA
I _{BM}	peak base current		–	–50	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	I _E = 0; V _{CB} = –200 V	–	–10	nA
		I _E = 0; V _{CB} = –200 V; T _j = 150 °C	–	–10	μA
I _{EBO}	emitter-base cut-off current	I _C = 0; V _{EB} = –5 V	–	–50	nA
h _{FE}	DC current gain	I _C = –25 mA; V _{CE} = –20 V	50	–	
V _{CEsat}	collector-emitter saturation voltage	I _C = –30 mA; I _B = –5 mA	–	–800	mV
C _{re}	feedback capacitance	I _C = I _c = 0; V _{CB} = –30 V; f = 1 MHz	–	1.6	pF
f _T	transition frequency	I _C = –10 mA; V _{CE} = –10 V; f = 100 MHz	60	–	MHz

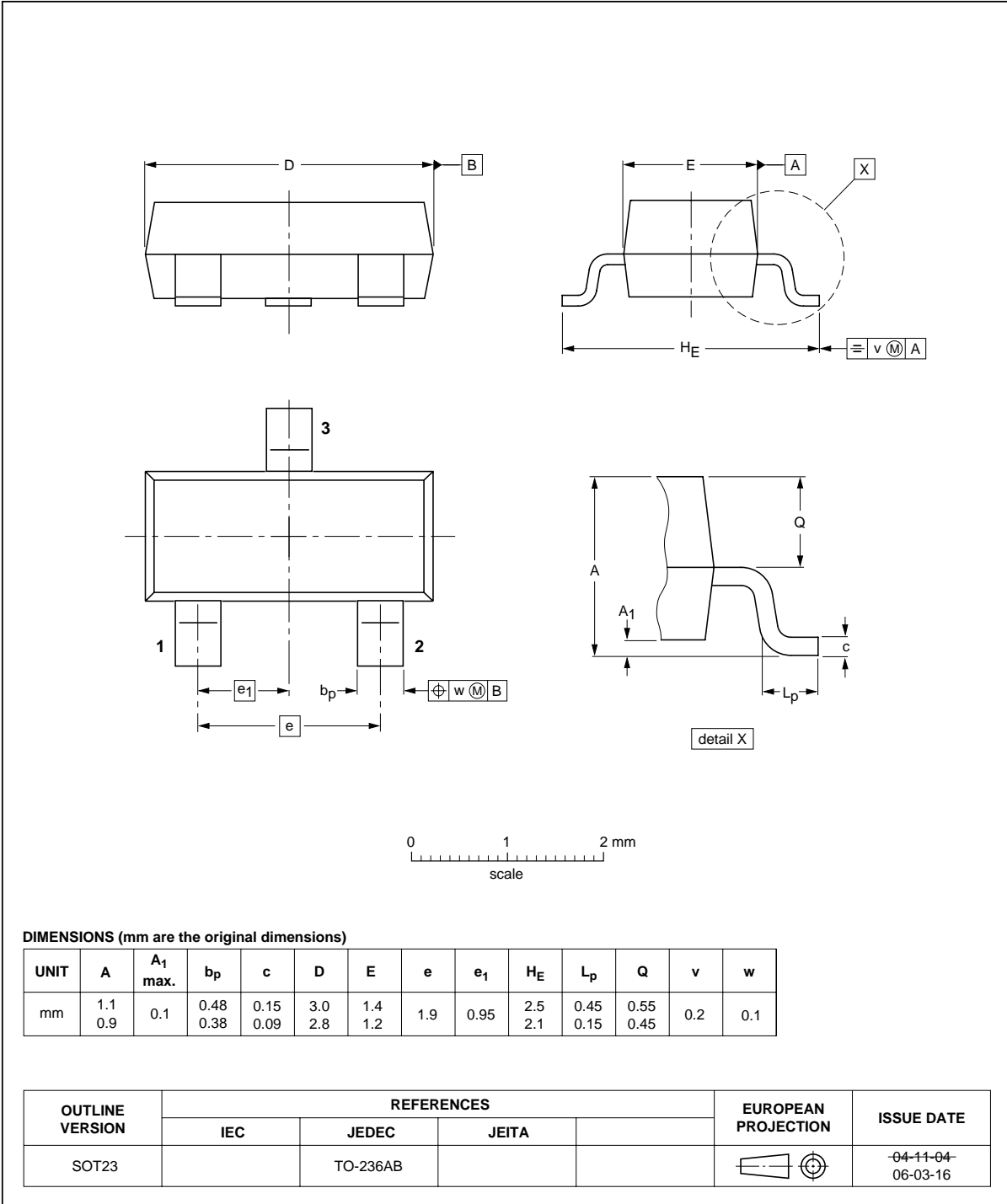
PNP high-voltage transistors

BF821; BF823

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



PNP high-voltage transistors

BF821; BF823

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: <http://www.nxp.com>

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